



**2023-2**

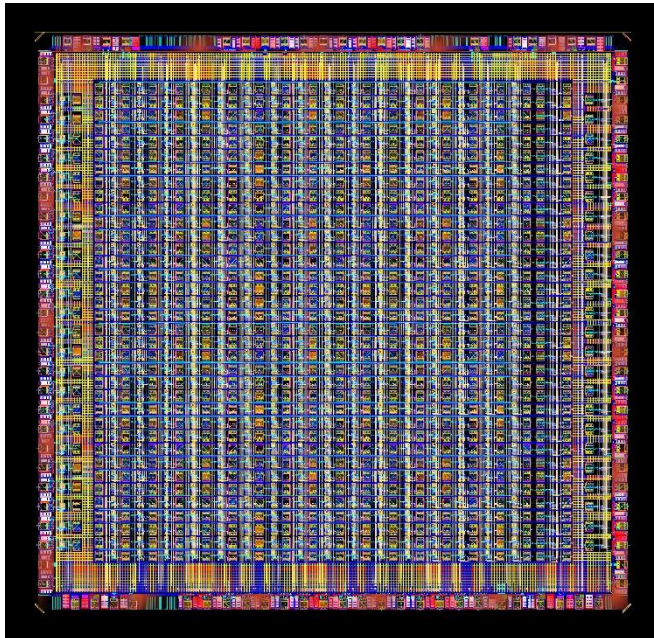
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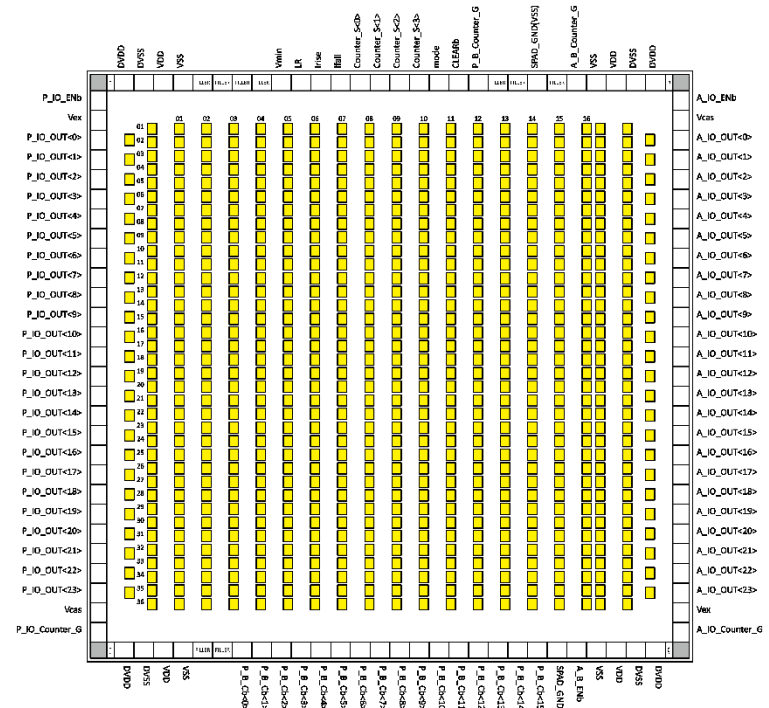
# Achievements

- **Process** : DBH 90nm CIS (BSI)
- **Area** : 4,460um × 4,350um
- **Design** : SPAD AFEs

- **Purpose**
  - 1) Detect sub-ns output pulse.
  - 2) Verify differences about output characteristic between 'I/O Pad' and 'Bond Pad'
  - 3) Designed SPAD verification.

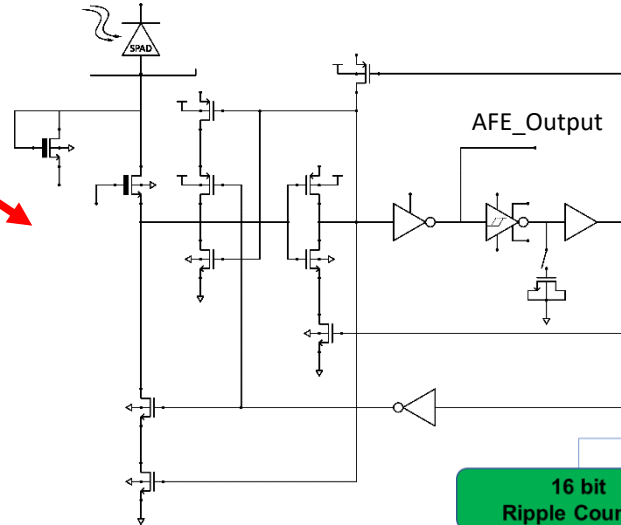
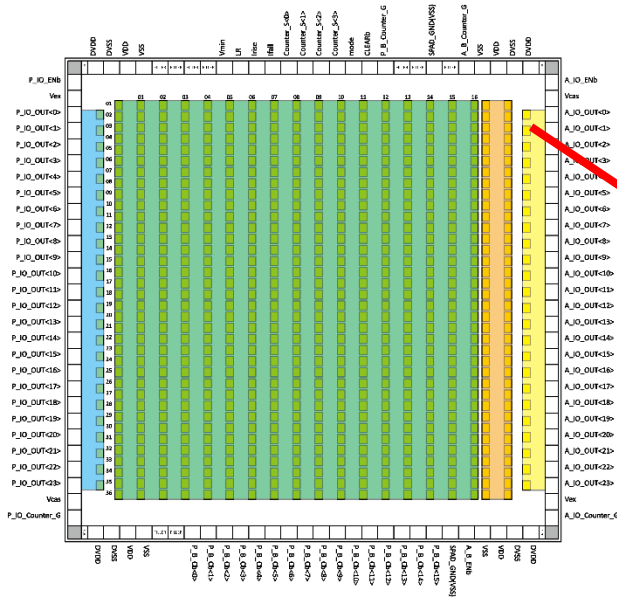


<TOP View>



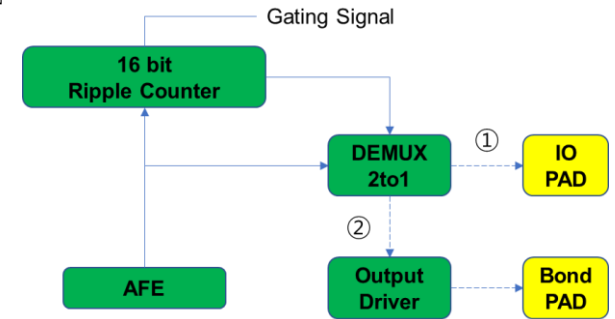
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# Achievements







<SPAD AFE>

<Read-out Stage>



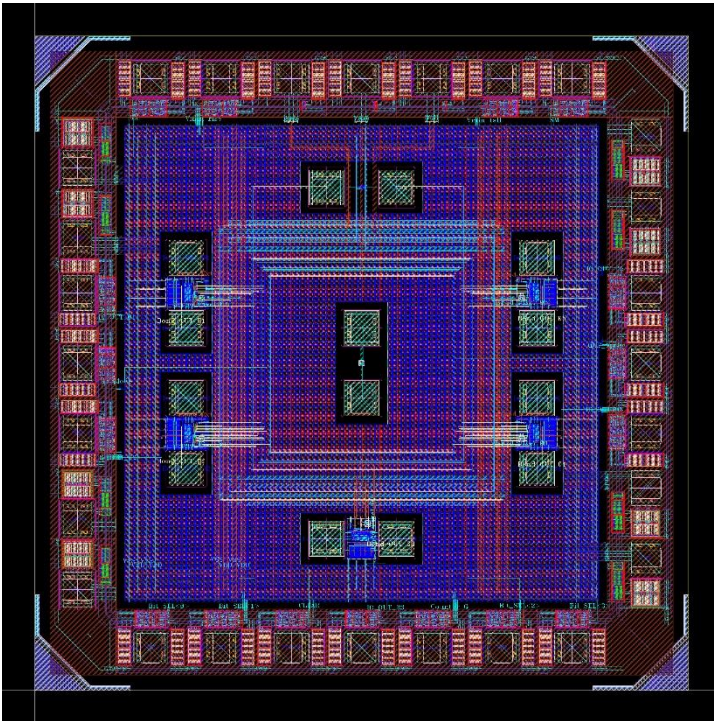
 Pixel IO PAD Read-Out	- SPAD Type #6 - AFE Type #4
 Pixel Bond PAD Read-Out	- SPAD Type #36 - AFE Type #4
 Only AFE Bond PAD Read-Out	- AFE Type #4
 Only AFE IO PAD Read-Out	- AFE Type #4

	IO_PAD	Bond_PAD
Pixel (SPAD+AFE)	 Pixel IO PAD Read-Out	 Pixel Bond PAD Read-Out
Only AFE	 Only AFE IO PAD Read-Out	 Only AFE Bond PAD Read-Out

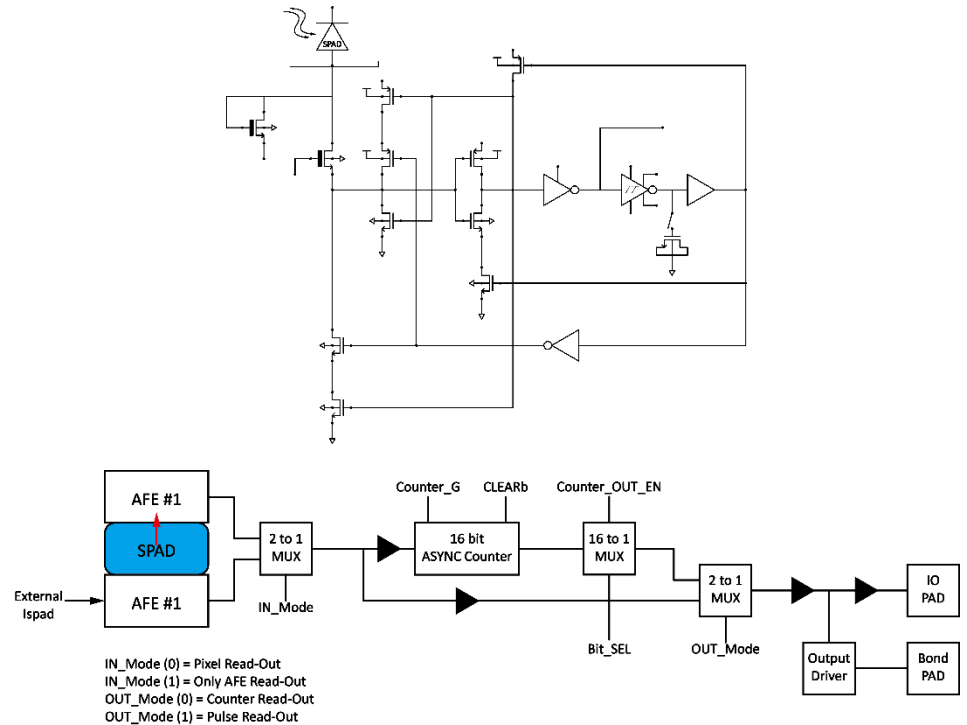
# Achievements

- **Process** : DBH 110nm CIS (BSI)
- **Area** : 1,490um × 1,490um
- **Design** : SPAD AFEs & Device

- **Purpose**
  - 1) Detect sub-ns output pulse.
  - 2) Verify differences about output characteristic between 'I/O Pad' and 'Bond Pad'
  - 3) Designed SPAD verification.



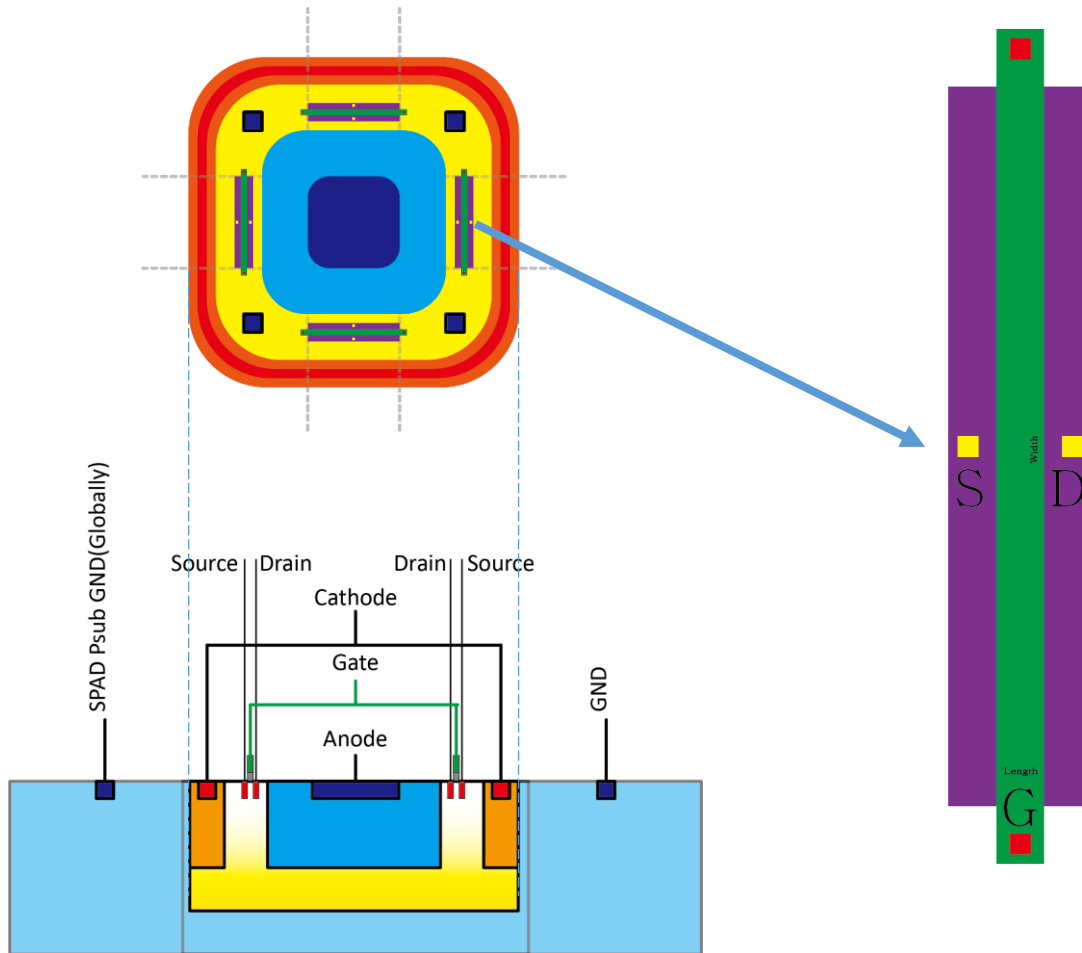
<TOP View>



<SPAD AFE & Read-out>

# Achievements

## <SPAD Integrated with MOSFET>



# Future Plan

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1. Imaging System Setup (w/JH Kim)
2. SPAD Device Measurement & Thesis Writing
3. Research & Design Large SPAD Array using Verified AFE